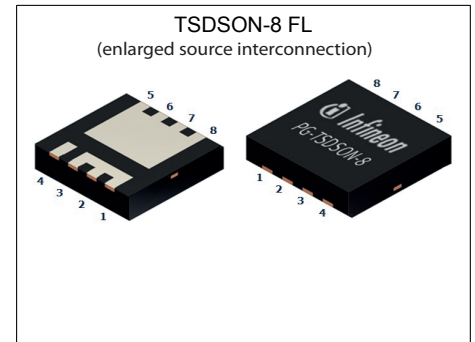


# MOSFET

## OptiMOS™ Power-MOSFET, 40 V

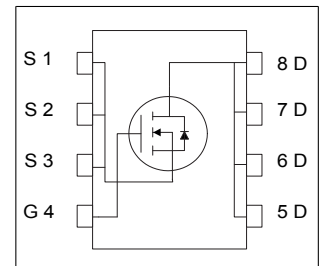
### Features

- Optimized for high performance SMPS, e.g. sync. rec.
- Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability with enlarged source interconnection



**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit |
|------------------|-------|------|
| $V_{DS}$         | 40    | V    |
| $R_{DS(on),max}$ | 2.8   | mΩ   |
| $I_D$            | 40    | A    |
| $Q_{OSS}$        | 28    | nC   |
| $Q_G(0V..10V)$   | 32    | nC   |



| Type / Ordering Code | Package        | Marking | Related Links |
|----------------------|----------------|---------|---------------|
| BSZ028N04LS          | PG-TSDSON-8 FL | 028N04L | -             |

<sup>1)</sup> J-STD20 and JESD22

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                     | Symbol            | Values |      |                            | Unit | Note / Test Condition                                                                                                                                                                                                                                              |
|-----------------------------------------------|-------------------|--------|------|----------------------------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                               |                   | Min.   | Typ. | Max.                       |      |                                                                                                                                                                                                                                                                    |
| Continuous drain current                      | $I_D$             | -      | -    | 40<br>40<br>40<br>40<br>21 | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=4.5\text{ V}$ , $T_C=25\text{ °C}$<br>$V_{GS}=4.5\text{ V}$ , $T_C=100\text{ °C}$<br>$V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=60\text{ K/W}^{(1)}$ |
| Pulsed drain current <sup>(2)</sup>           | $I_{D,pulse}$     | -      | -    | 160                        | A    | $T_C=25\text{ °C}$                                                                                                                                                                                                                                                 |
| Avalanche energy, single pulse <sup>(3)</sup> | $E_{AS}$          | -      | -    | 100                        | mJ   | $I_D=20\text{ A}$ , $R_{GS}=25\text{ }\Omega$                                                                                                                                                                                                                      |
| Gate source voltage                           | $V_{GS}$          | -20    | -    | 20                         | V    | -                                                                                                                                                                                                                                                                  |
| Power dissipation                             | $P_{tot}$         | -      | -    | 63<br>2.1                  | W    | $T_C=25\text{ °C}$<br>$T_A=25\text{ °C}$ , $R_{thJA}=60\text{ K/W}^{(1)}$                                                                                                                                                                                          |
| Operating and storage temperature             | $T_j$ , $T_{stg}$ | -55    | -    | 150                        | °C   | IEC climatic category;<br>DIN IEC 68-1: 55/150/56                                                                                                                                                                                                                  |

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter                                                       | Symbol     | Values |      |      | Unit | Note / Test Condition |
|-----------------------------------------------------------------|------------|--------|------|------|------|-----------------------|
|                                                                 |            | Min.   | Typ. | Max. |      |                       |
| Thermal resistance, junction - case                             | $R_{thJC}$ | -      | 1.2  | 2    | K/W  | -                     |
| Device on PCB,<br>6 cm <sup>2</sup> cooling area <sup>(1)</sup> | $R_{thJA}$ | -      | -    | 60   | K/W  | -                     |

<sup>(1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>(2)</sup> See Diagram 3 for more detailed information

<sup>(3)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |            |            | Unit          | Note / Test Condition                                                                                                               |
|----------------------------------|---------------|--------|------------|------------|---------------|-------------------------------------------------------------------------------------------------------------------------------------|
|                                  |               | Min.   | Typ.       | Max.       |               |                                                                                                                                     |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 40     | -          | -          | V             | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                                                                                             |
| Gate threshold voltage           | $V_{GS(th)}$  | 1.2    | -          | 2          | V             | $V_{DS}=4.5\text{ V}$ , $T_C=100\text{ °C}$                                                                                         |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.1<br>10  | 1<br>100   | $\mu\text{A}$ | $V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=25\text{ °C}$<br>$V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=125\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 10         | 100        | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                                                                                          |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 2.2<br>2.7 | 2.8<br>3.8 | m $\Omega$    | $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$<br>$V_{GS}=4.5\text{ V}$ , $I_D=20\text{ A}$                                               |
| Gate resistance <sup>1)</sup>    | $R_G$         | -      | 0.9        | 1.8        | $\Omega$      | -                                                                                                                                   |
| Transconductance                 | $g_{fs}$      | 50     | 100        | -          | S             | $ V_{DS} >2 I_D /R_{DS(on)max}$ , $I_D=20\text{ A}$                                                                                 |

**Table 5 Dynamic characteristics**

| Parameter                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                                              |
|--------------------------------------------|--------------|--------|------|------|------|----------------------------------------------------------------------------------------------------|
|                                            |              | Min.   | Typ. | Max. |      |                                                                                                    |
| Input capacitance <sup>1)</sup>            | $C_{iss}$    | -      | 2300 | 3220 | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$                                      |
| Output capacitance <sup>1)</sup>           | $C_{oss}$    | -      | 640  | 900  | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$                                      |
| Reverse transfer capacitance <sup>1)</sup> | $C_{rss}$    | -      | 52   | 104  | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=20\text{ V}$ , $f=1\text{ MHz}$                                      |
| Turn-on delay time                         | $t_{d(on)}$  | -      | 5    | -    | ns   | $V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Rise time                                  | $t_r$        | -      | 4    | -    | ns   | $V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Turn-off delay time                        | $t_{d(off)}$ | -      | 37   | -    | ns   | $V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |
| Fall time                                  | $t_f$        | -      | 4    | -    | ns   | $V_{DD}=20\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ ,<br>$R_{G,ext}=1.6\text{ }\Omega$ |

**Table 6 Gate charge characteristics<sup>2)</sup>**

| Parameter                          | Symbol        | Values |      |      | Unit | Note / Test Condition                                                        |
|------------------------------------|---------------|--------|------|------|------|------------------------------------------------------------------------------|
|                                    |               | Min.   | Typ. | Max. |      |                                                                              |
| Gate to source charge              | $Q_{gs}$      | -      | 5.5  | -    | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate charge at threshold           | $Q_{g(th)}$   | -      | 3.6  | -    | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate to drain charge <sup>1)</sup> | $Q_{gd}$      | -      | 5.1  | 7.1  | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Switching charge                   | $Q_{sw}$      | -      | 6.9  | -    | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate charge total <sup>1)</sup>    | $Q_g$         | -      | 32   | 45   | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate plateau voltage               | $V_{plateau}$ | -      | 2.4  | -    | V    | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$  |
| Gate charge total <sup>1)</sup>    | $Q_g$         | -      | 16   | 22   | nC   | $V_{DD}=20\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge total, sync. FET       | $Q_{g(sync)}$ | -      | 13   | -    | nC   | $V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }4.5\text{ V}$                    |
| Output charge <sup>1)</sup>        | $Q_{oss}$     | -      | 28   | 39   | nC   | $V_{DD}=20\text{ V}$ , $V_{GS}=0\text{ V}$                                   |

<sup>1)</sup> Defined by design. Not subject to production test

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

| Parameter                           | Symbol        | Values |      |      | Unit | Note / Test Condition                                                      |
|-------------------------------------|---------------|--------|------|------|------|----------------------------------------------------------------------------|
|                                     |               | Min.   | Typ. | Max. |      |                                                                            |
| Diode continuous forward current    | $I_S$         | -      | -    | 40   | A    | $T_C=25\text{ °C}$                                                         |
| Diode pulse current                 | $I_{S,pulse}$ | -      | -    | 160  | A    | $T_C=25\text{ °C}$                                                         |
| Diode forward voltage               | $V_{SD}$      | -      | 0.81 | 1    | V    | $V_{GS}=0\text{ V}$ , $I_F=20\text{ A}$ , $T_j=25\text{ °C}$               |
| Reverse recovery time <sup>1)</sup> | $t_{rr}$      | -      | 24   | 48   | ns   | $V_R=20\text{ V}$ , $I_F=20\text{ A}$ , $di_F/dt=400\text{ A/}\mu\text{s}$ |
| Reverse recovery charge             | $Q_{rr}$      | -      | 57   | -    | nC   | $V_R=20\text{ V}$ , $I_F=20\text{ A}$ , $di_F/dt=400\text{ A/}\mu\text{s}$ |

<sup>1)</sup> Defined by design. Not subject to production test

## 4 Electrical characteristics diagrams

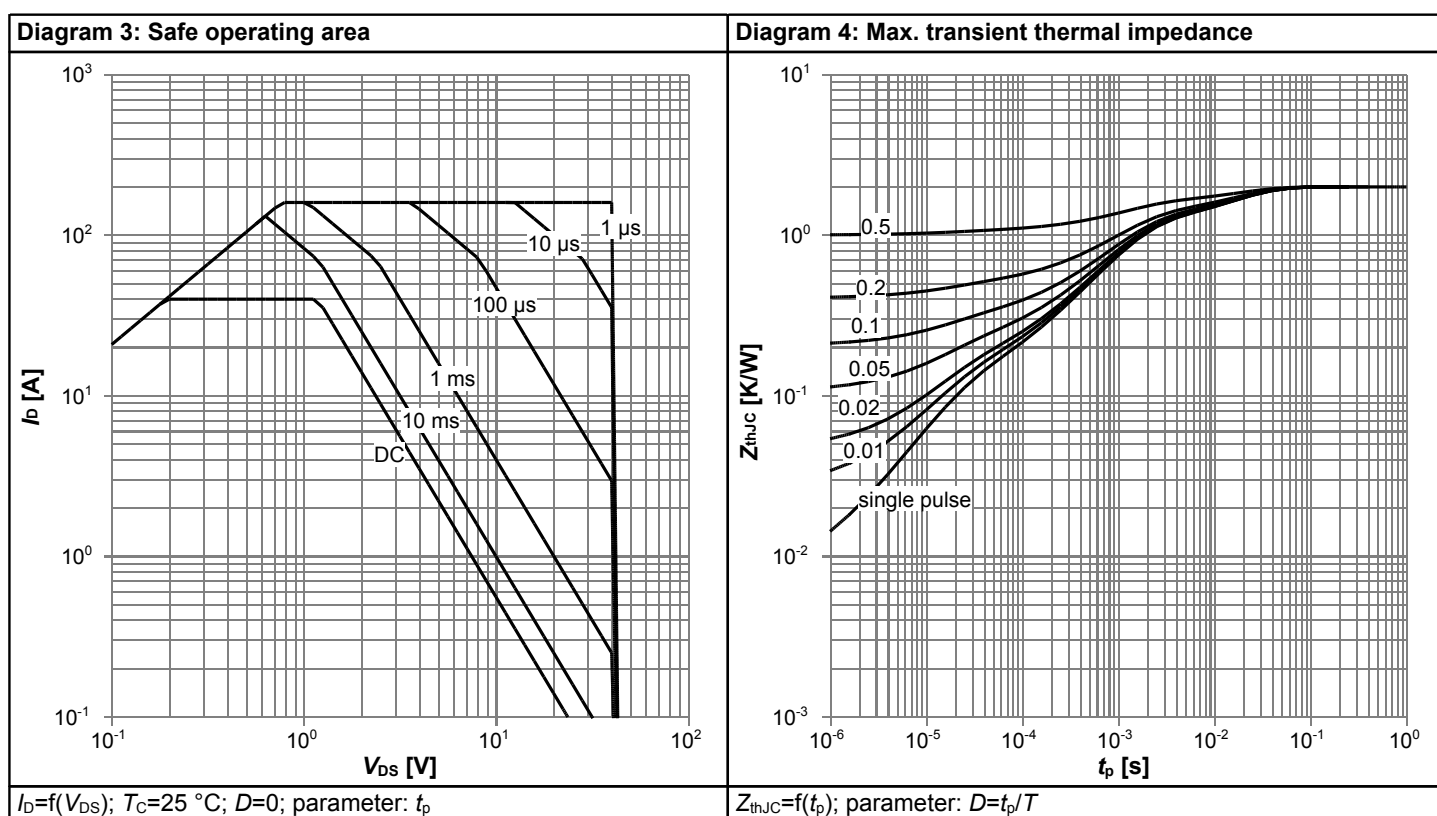
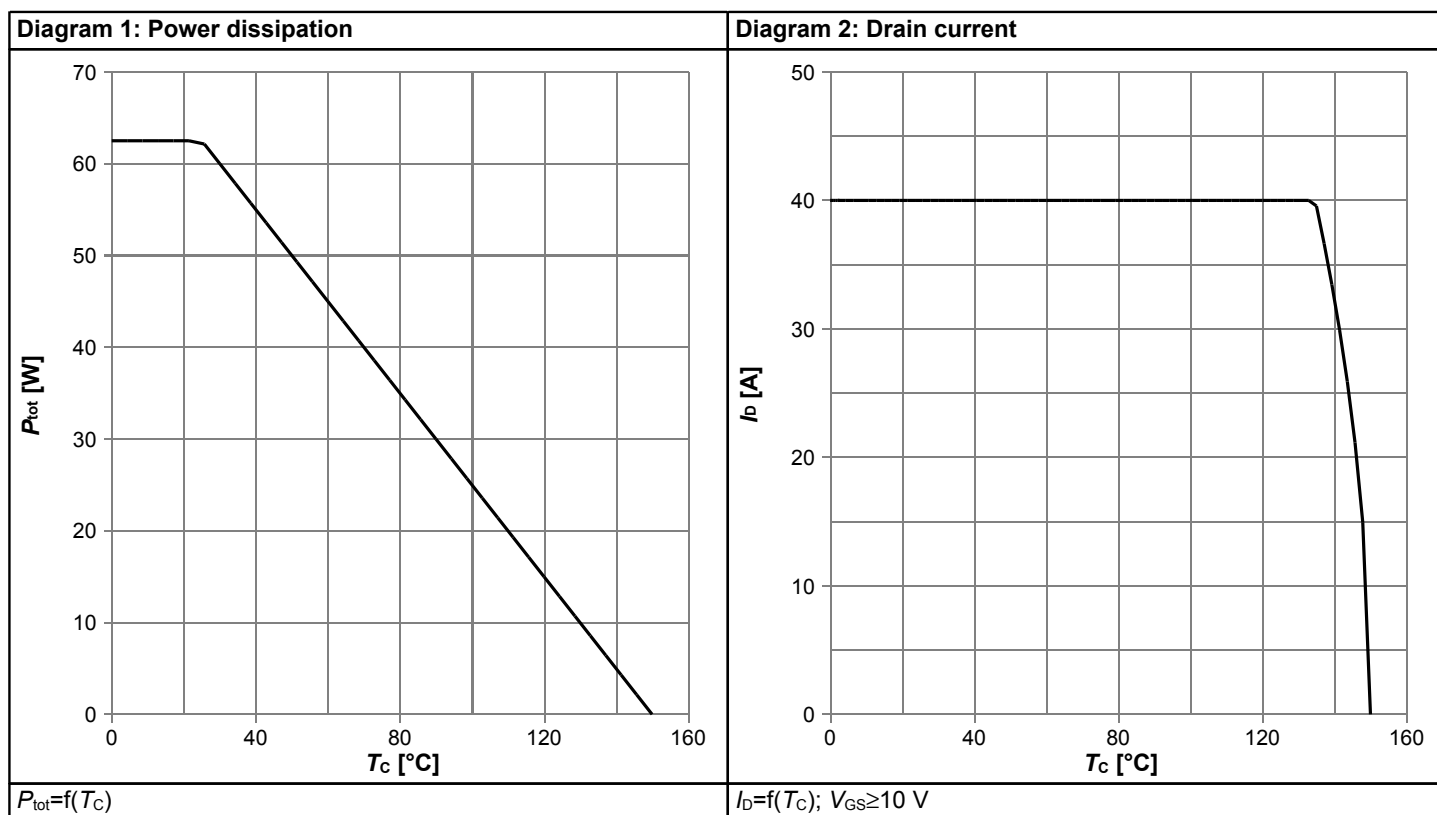
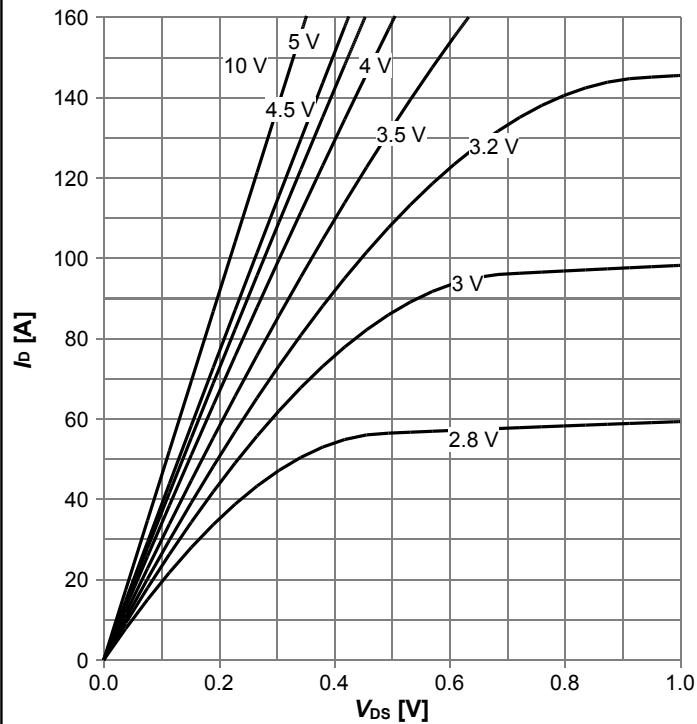
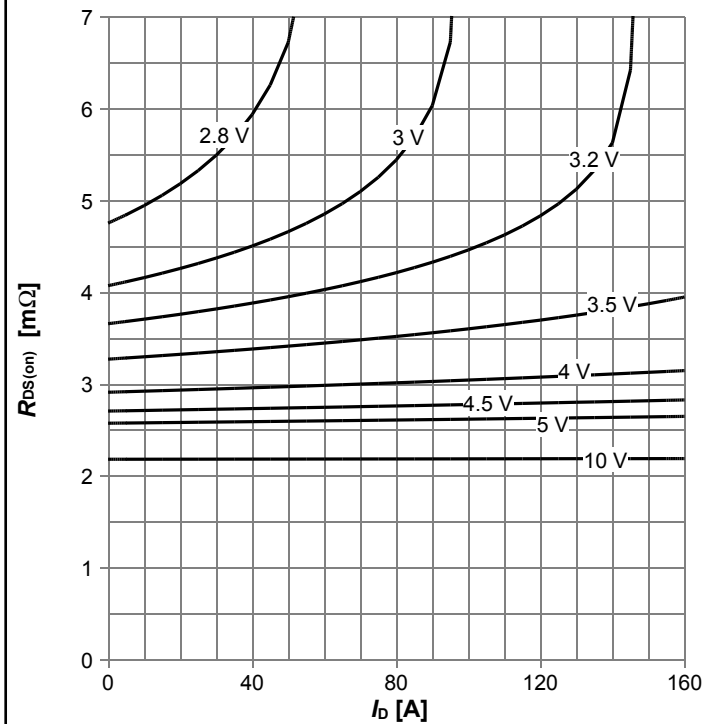


Diagram 5: Typ. output characteristics



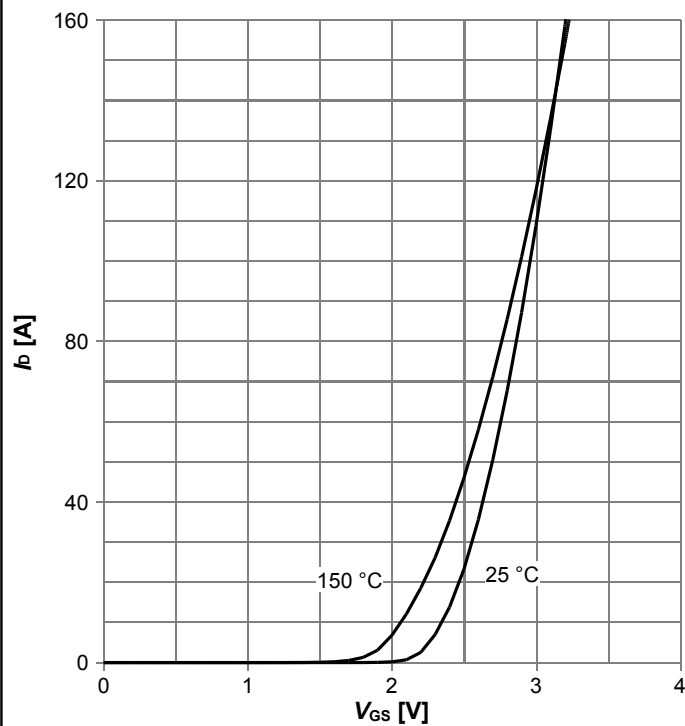
$I_D = f(V_{DS})$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



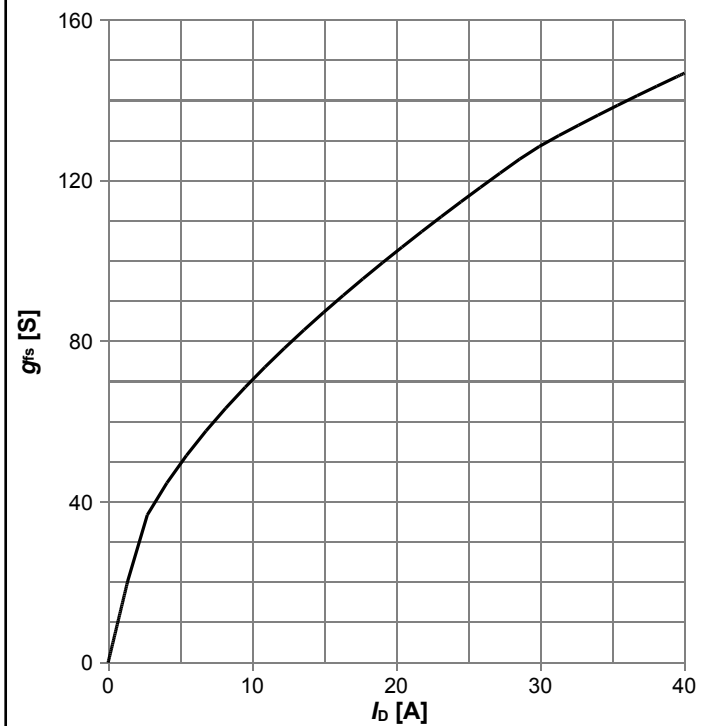
$R_{DS(on)} = f(I_D)$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



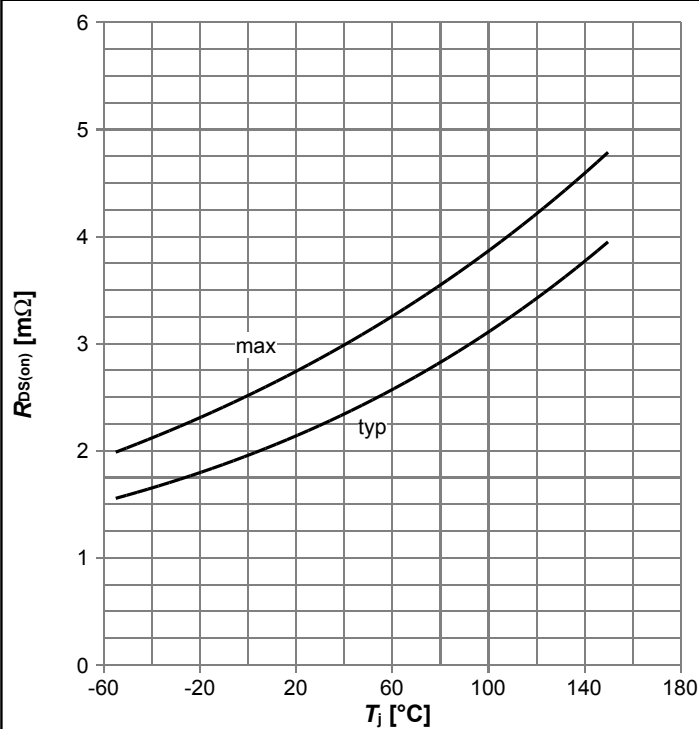
$I_D = f(V_{GS})$ ;  $|V_{DS}| > 2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. forward transconductance



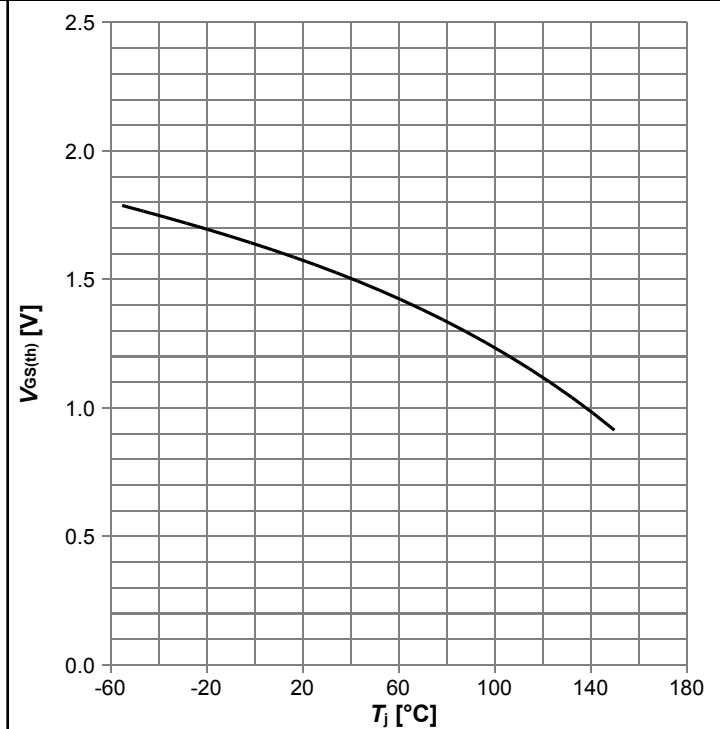
$g_{fs} = f(I_D)$ ;  $T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



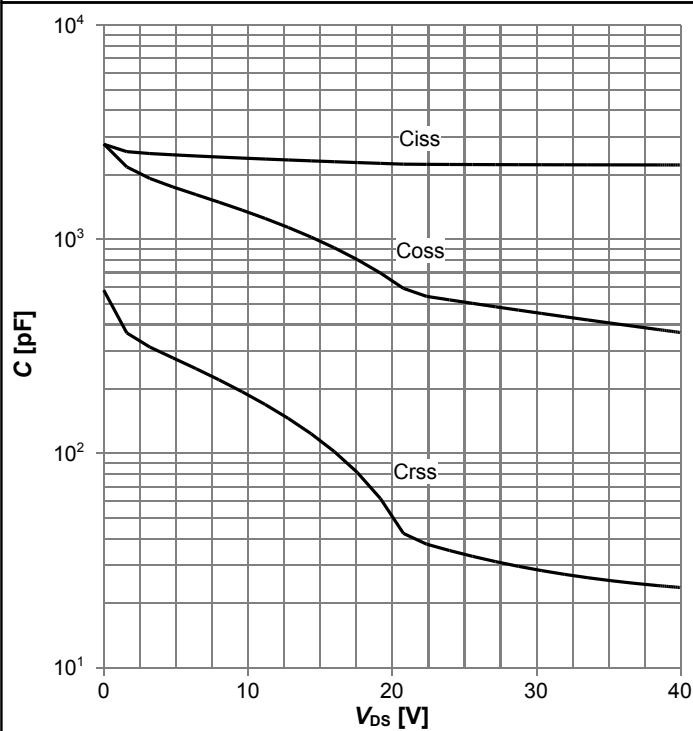
$R_{DS(on)}=f(T_j)$ ;  $I_D=20$  A;  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



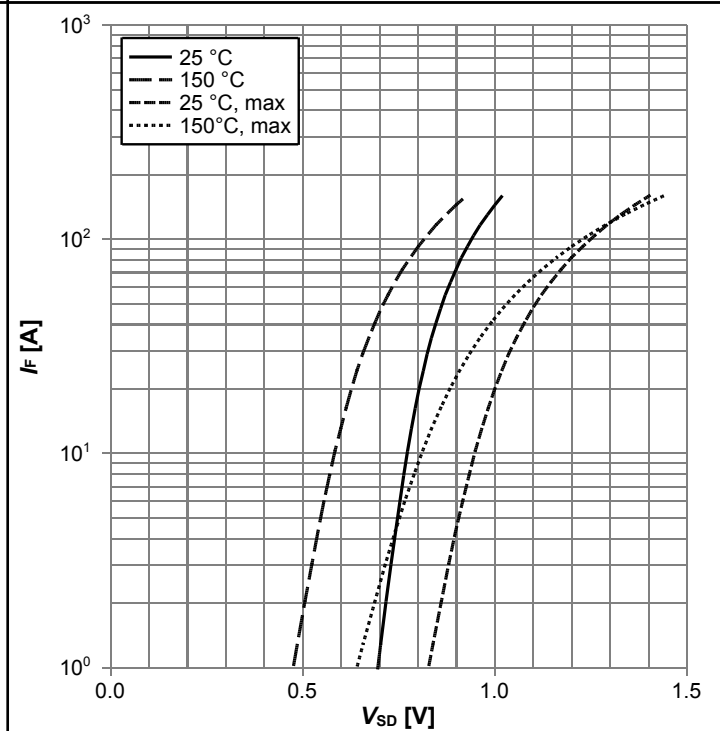
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$ ;  $I_D=250$   $\mu$ A

Diagram 11: Typ. capacitances



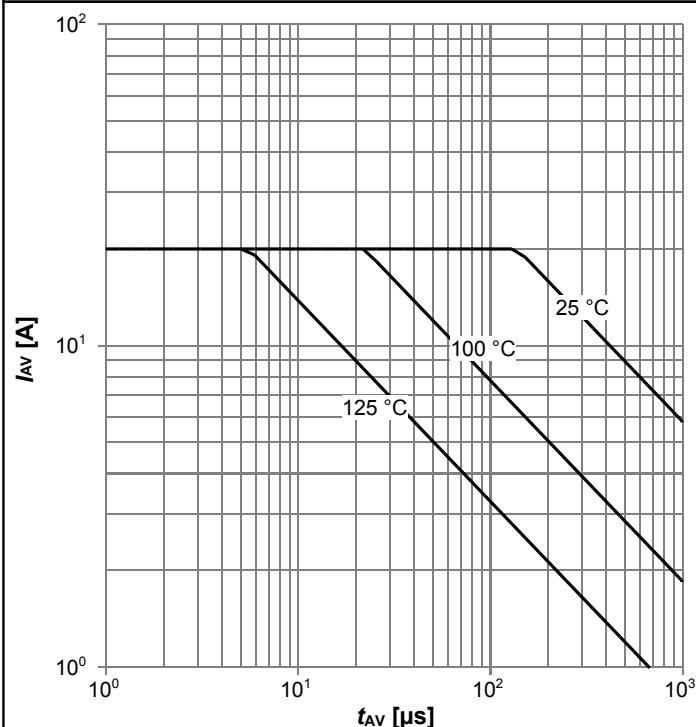
$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

Diagram 12: Forward characteristics of reverse diode



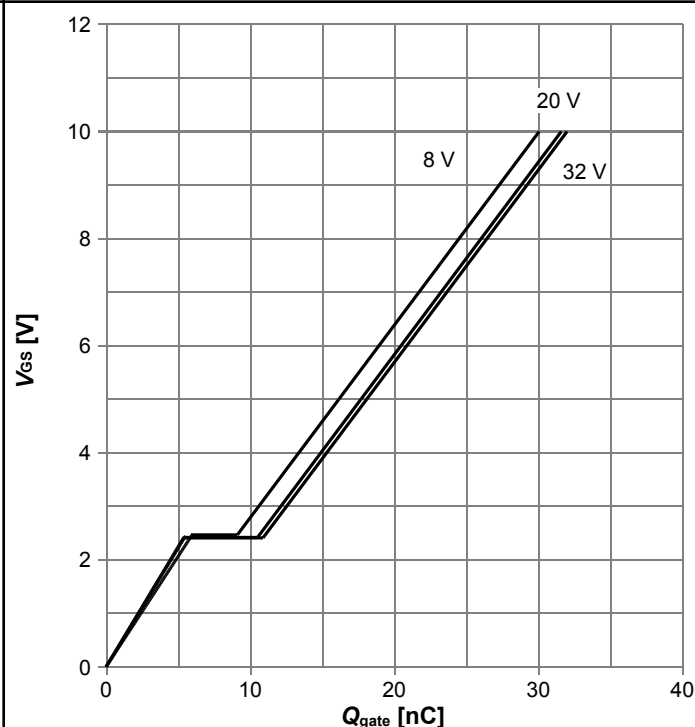
$I_F=f(V_{SD})$ ; parameter:  $T_j$

Diagram 13: Avalanche characteristics



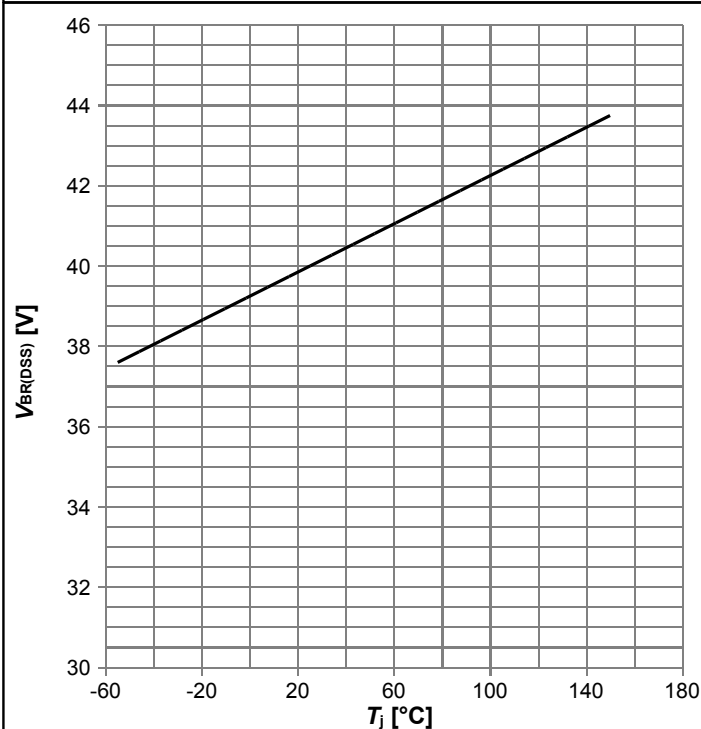
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25\ \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate})$ ;  $I_D=20\text{ A}$  pulsed; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_J)$ ;  $I_D=1\text{ mA}$

Gate charge waveforms



## 5 Package Outlines

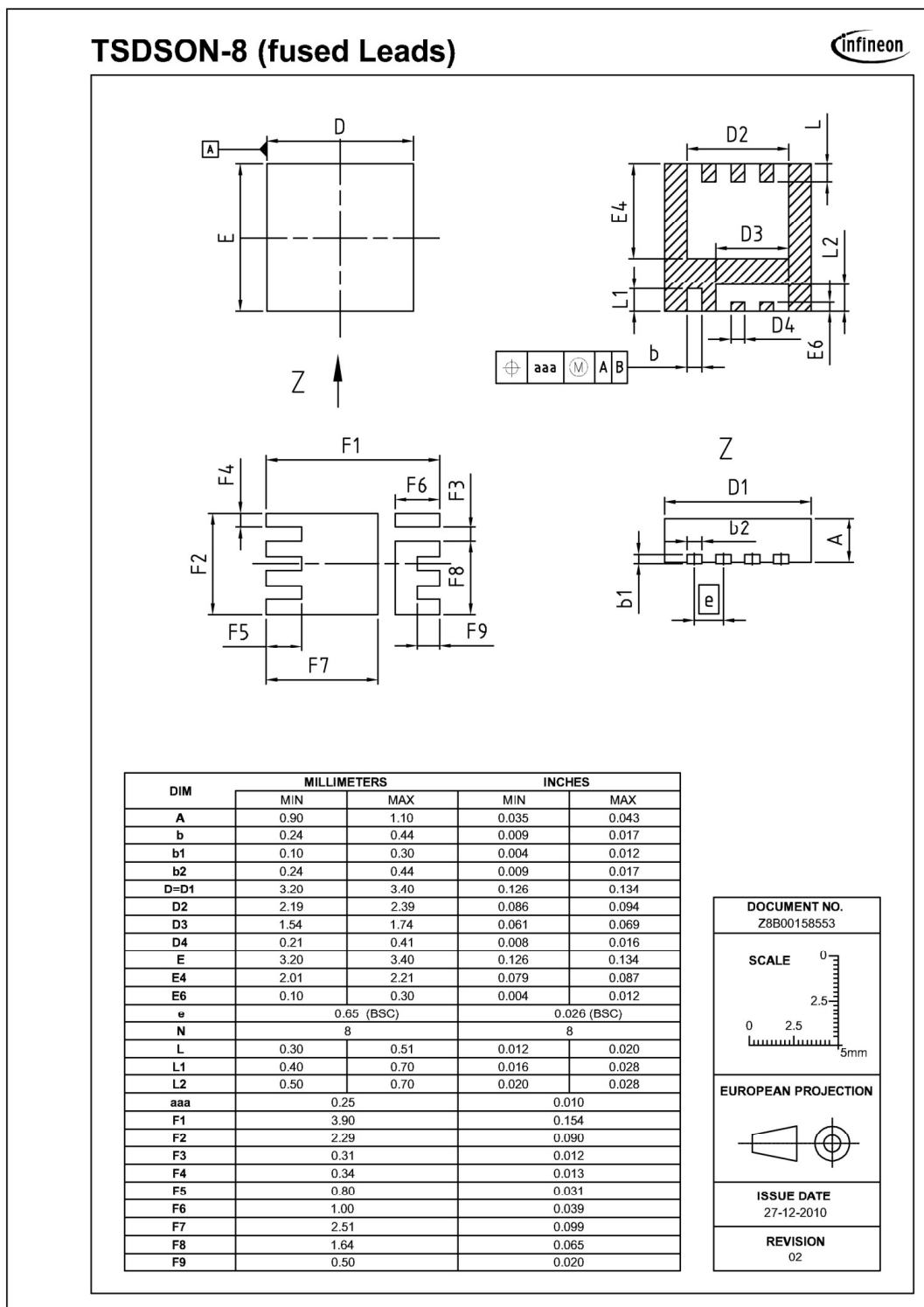


Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

## Revision History

BSZ028N04LS

**Revision: 2016-06-09, Rev. 2.1**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 2.1      | 2016-06-09 | Insert max values and update footnotes       |

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